

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



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11/29/07
SIC
First Named Inventor:

Application No.: 10/796,514
Filing Date: 03/09/2004

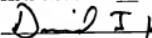
Title: TRANSISTOR HAVING HIGH DIELECTRIC GATE INSULATING LAYER AND SOURCE AND DRAIN FORMING SCHOTTKY CONTACT WITH SUBSTRATE

Confirmation No.: 1961
Examiner: Kim, Su C
Group Art Unit: 2823

RESPONSE AFTER FINAL UNDER 37 C.F.R. 1.116

Mail Stop AF
Commissioner for Patents
P.O. Box 1450
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I hereby certify that this document is being sent via First Class U.S. mail addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on this 13 day of November, 2007.


(Signature)

Dear Sir:

Applicant hereby submits a response to the Final Office Action dated June 11, 2007.

Claims are reflected in the listing of claims which begins on page 2 of this paper. Claims 1, 15, 24, 33, 44 and 55 have been amended to patentably distinguish the present invention over the cited prior art.

Remarks/Arguments begin on page 11 of this paper.